

# Conduction-cooled QCW Stacked Array

QD-Q1yzz-A / QD-Q1yzz-B / QD-Q1yzz-BS / QD-Q1yzz-G / QD-Q1yzz-K

#### **DESCRIPTION**

QD-Q1yzz-A, QD-Q1yzz-B, QD-Q1yzz-BS, QD-Q1yzz-G and QD-Q1yzz-K are a variety of conductively cooled laser diode stacked arrays. These Stacks can be built from 1 to 19 diode bars of 60W QCW to 400W QCW. The laser diode bar arrays benefit from a fully mastered technology, with the appropriate design for improved efficiency and reliable operation. Packaging and heat-sink have been optimized to reduce the overall thermal resistance. Assembly in a compact and rugged package, using AuSn hard solder, allows easy connection to a heat exchanger to get good thermal control.

This technology of stacks has been successfully submitted to specific environmental tests requested for Space missions (long life-tests, endurance under vacuum, irradiations...) with NASA or ESA.

These stacks are ideal for different applications under severe conditions: pumping rods or slabs solid state lasers, illuminators...for aerospace, industrial, space applications.

### **MAIN FEATURES**



- 60W to 400W QCW per diode bar
- Standard wavelength: from 790 to 980 nm
- Vacuum qualified technology
- Low thermal resistance assembly
- Mechanically robust, shock and vibration resistant

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t	P/bar	60	80	100	125	150	200

1

808

2

790

3

830

4

915

5

940

6

980

300 400

8 9

nm

W

#### **SPECIFICATIONS**

PARAMETERS @ 25℃	QD-Qxyzz-A	QD-Qxyzz-B	QD-Qxyzz-BS	QD-Qxyzz-G	QD-Qxyzz-K	Units	
Number of Diode bars zz =	2 to 06	1 to 12	1 to 19	1 to 16	1 to 08		
Pitch between diode bars		330 to few 1000s					
Emitting area		10 x (zz – 1)* pitch					
QCW Optical Power per Diode B	ar	up to 400					
QCW Optical Power	up to 2 400	up to 4 400	up to 7 000	up to 6 000	up to 1 600	W	
Operating current @ 100W / b	ar	95 A Typical - 115A Max					
Operating current @ 200W / b	ng current @ 200W / bar 185 A Typical - 215A Max				А		
Operating current @ 400W / b	ar	370 A Typical - 390A Max				А	
Operating voltage		<2 V /bar					
Total efficiency		58% @ 808 nm, 65% @ 940/980 nm					
Wavelength		790 to 980					
Spectral width (FWHM)		3					
Beam divergence (FWHM)		9 X 36					

x =

λ

#### Note :

- Standard Polarisation: TM or TE mode @ 808 nm, TE @ 9xx nm
- Variation of wavelength with temperature is approximately 0.26 nm/°C
- Tolerance on wavelength is +/- 3nm, +/- 1,5 nm on demand
- Double or Triple Quantum Well bars available (ex: 400W @ 200A & 4V)
- Specifications are for nominal lifetime > 1. 10<sup>9</sup> pulses (for 200µs pulse width)

Quantel Laser Diodes reserves the right to change specifications without prior notice



#### **ABSOLUTE MAXIMUM RATINGS**

PARAMETERS	QD-Qxyzz-A	QD-Qxyzz-B	QD-Qxyzz-BS	QD-Qxyzz-G	QD-Qxyzz-K	
Pulse width	500				μs	
Maximum duty cycle	3	4			%	
Reverse voltage	3					Volt
Storage temperature			-55 to +85			°C

Note : Operation at temperature below dew point requests to use dry N2 environment

### **PACKAGE SPECIFICATIONS**

- dimensions are in mm
- standard tolerances are + 0.2 mm







## QD-Q1yzz-B



This stack "B" type can be proposed with a variable number ('zz') of diode bars: 'zz' = 1 to 12 bars at a pitch of  $330\mu m$ , 'zz' = 1 to 11 bars at a pitch of 400um.

'zz'= 1 to 8 bars at a pitch of  $500\mu m$ 



### **QD-Q1yzz-BS**



This stack "BS" type can be proposed with a variable number ('zz') of diode bars: 'zz' = 1 to 19 bars at a pitch of 400 $\mu$ m, 'zz' = 1 to 15 bars at a pitch of 500 $\mu$ m 'zz' = 1 to 6 bars at a pitch of

'zz' = 1 to 6 bars at a pitch of  $1000\mu m$ 

**NUANTE** laser diodes



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### QD-Q1yzz-K



This stack "Z" type offers a very small foot-print. It can be proposed with a

variable number of 'zz' diode bars: 'zz' = 1 to 8 bars at a pitch of

 $400\mu m$ ,

'zz'= 1 to 6 bars at a pitch of 500 $\mu m$ 





## <u>QD-Q1yzz-G</u>



This stack "BS" type can be proposed with a variable number ('zz') of diode bars: 'zz' = 1 to 19 bars at a pitch of 400 $\mu$ m, 'zz' = 1 to 15 bars at a pitch of 500 $\mu$ m 'zz' = 1 to 6 bars at a pitch of 1000 $\mu$ m

> Quante laser diodes



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